

NVD6828NL

MOSFET – Power, Single N-Channel

90 V, 20 mΩ, 41 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	90	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1 & 3)	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	41	A
		$T_C = 100^{\circ}\text{C}$		29	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^{\circ}\text{C}$	P_D	83	W
		$T_C = 100^{\circ}\text{C}$		42	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2 & 3)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	8.7	A
		$T_A = 100^{\circ}\text{C}$		6.1	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	3.8	W
		$T_A = 100^{\circ}\text{C}$		1.9	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$	I_{DM}	206	A	
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to 175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	40	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $V_{GS} = 10\text{ V}$, $I_{L(pk)} = 24.5\text{ A}$, $L = 0.3\text{ mH}$, $R_G = 25\text{ }\Omega$)			E_{AS}	90	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain)	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	40	

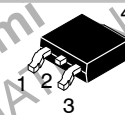
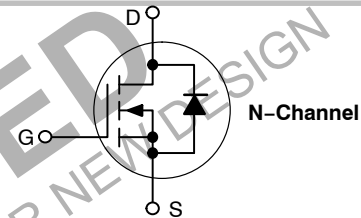
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



ON Semiconductor®

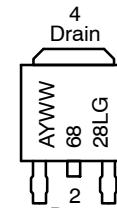
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$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
90 V	20 mΩ @ 10 V	41 A
	25 mΩ @ 4.5 V	



DPAK
CASE 369C
STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENT



1 Drain 3
Gate Source

- A = Assembly Location*
Y = Year
WW = Work Week
6828L = Device Code
G = Pb-Free Package

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejector pin), the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping†
NVD6828NLT4G	DPAK (Pb-Free)	2500/Tape & Reel
NVD6828NLT4G-VF01	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	90			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			87		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 90\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-6.5		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		16.5	20	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		19.1	25	

CHARGES, CAPACITANCES AND GATE RESISTANCES

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		2900		pF
Output Capacitance	C_{oss}			175		
Reverse Transfer Capacitance	C_{rss}			126		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 72\text{ V}, I_D = 20\text{ A}$		32		nC
		$V_{GS} = 10\text{ V}, V_{DS} = 72\text{ V}, I_D = 20\text{ A}$		61		
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 10\text{ V}, V_{DS} = 72\text{ V}, I_D = 20\text{ A}$		3.3		
Gate-to-Source Charge	Q_{GS}			9.0		
Gate-to-Drain Charge	Q_{GD}			16		

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DD} = 72\text{ V}, I_D = 20\text{ A}, R_G = 2.5\text{ }\Omega$		14		ns
Rise Time	t_r			64		
Turn-Off Delay Time	$t_{d(off)}$			28		
Fall Time	t_f			43		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$	$T_J = 25^\circ\text{C}$		0.84	1.2	V
			$T_J = 125^\circ\text{C}$		0.72		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 20\text{ A}$			35		ns
Charge Time	t_a				25		
Discharge Time	t_b				10		
Reverse Recovery Charge	Q_{RR}				49		nC

4. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

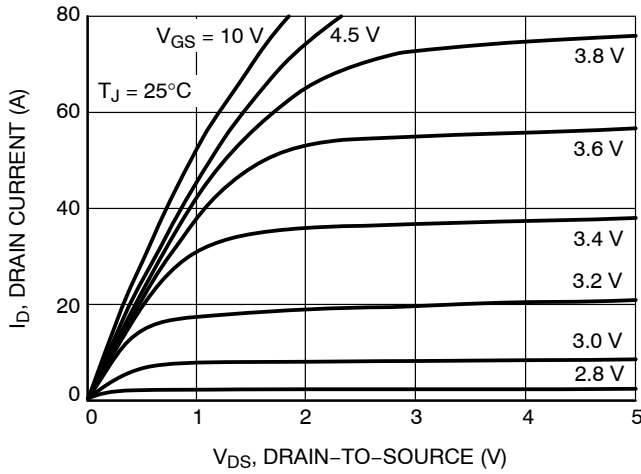


Figure 1. On-Region Characteristics

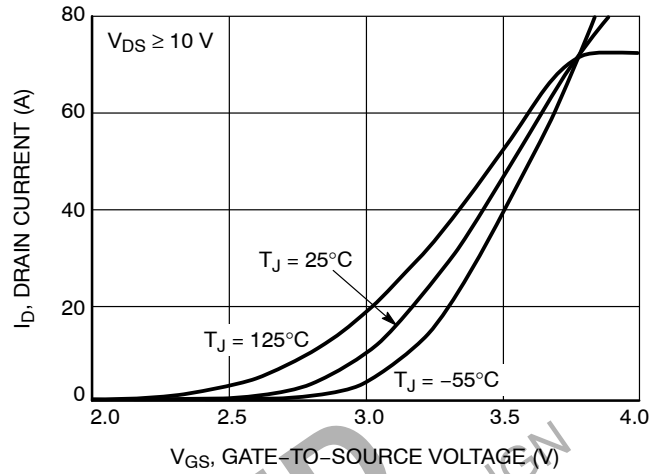


Figure 2. Transfer Characteristics

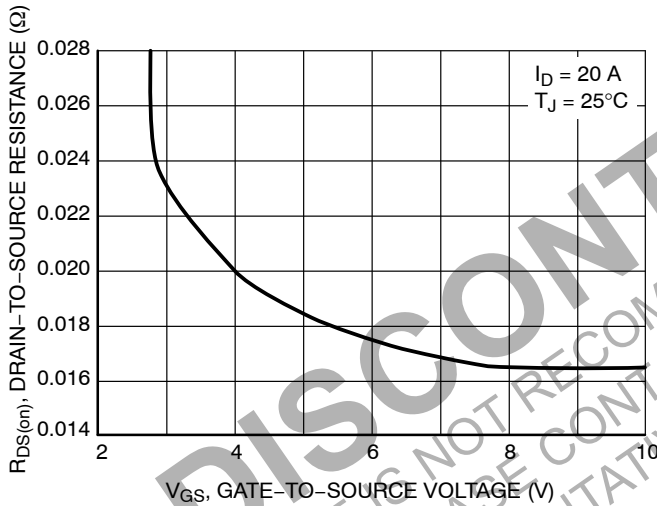


Figure 3. On-Resistance vs. Gate Voltage

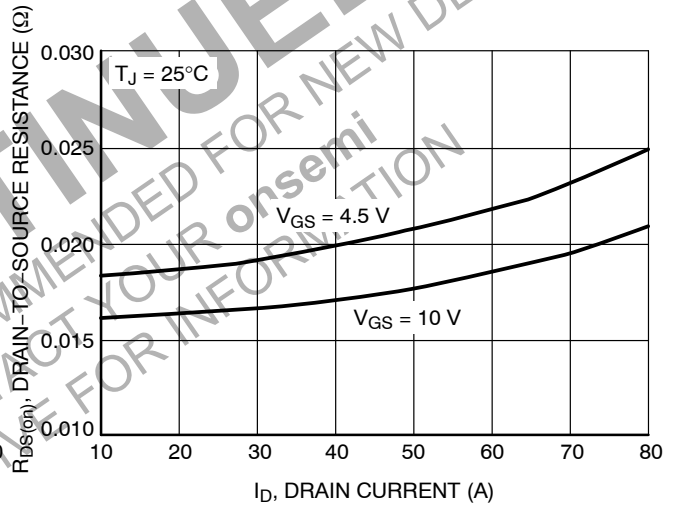


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

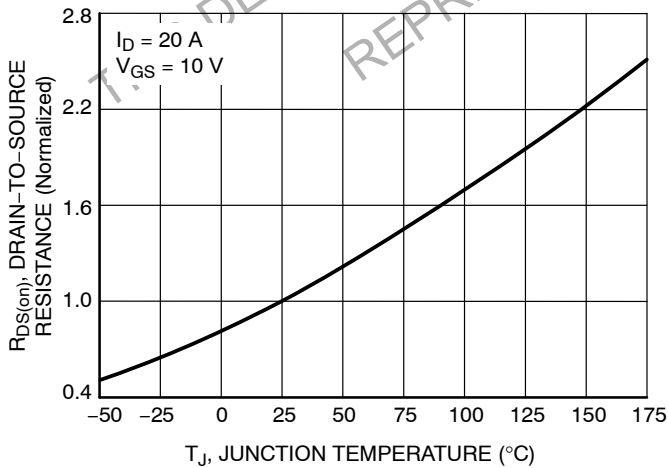


Figure 5. On-Resistance Variation with Temperature

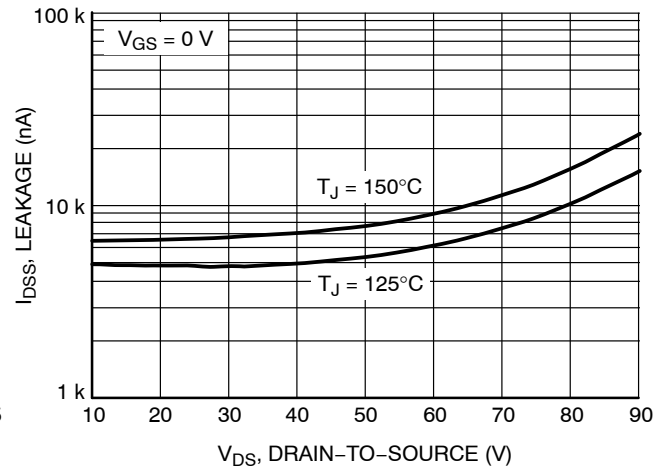


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

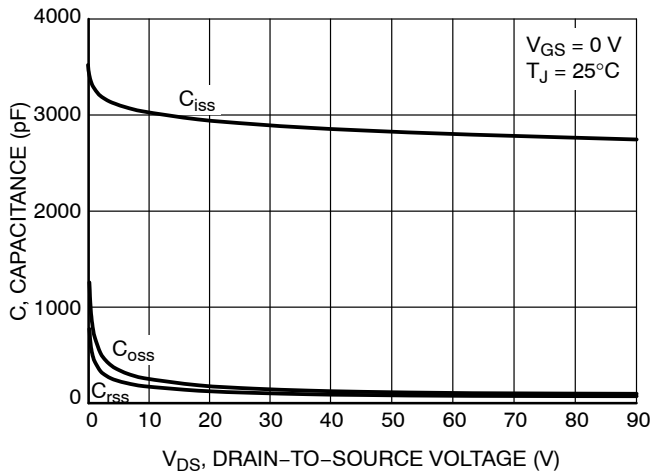


Figure 7. Capacitance Variation

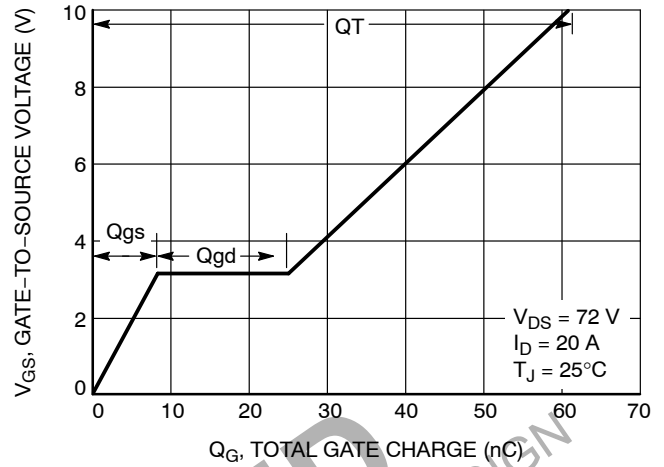


Figure 8. Gate-to-Source Voltage vs. Total Charge

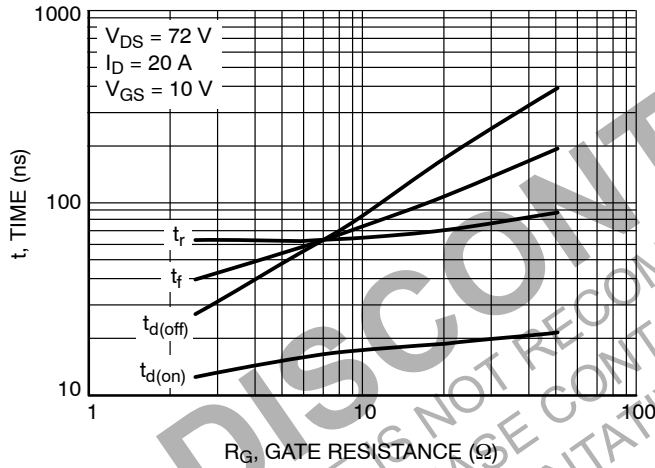


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

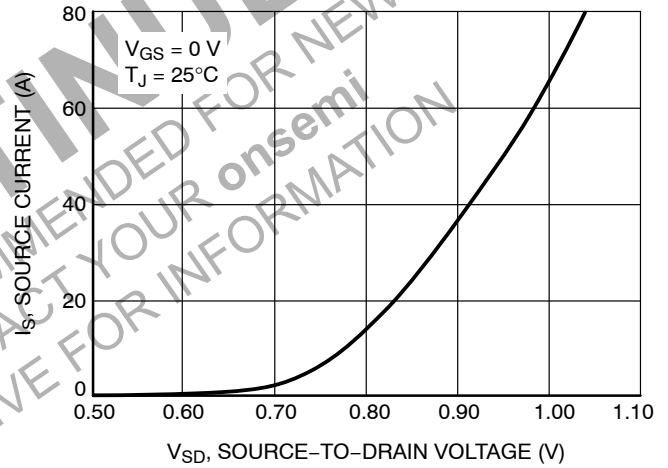


Figure 10. Diode Forward Voltage vs. Current

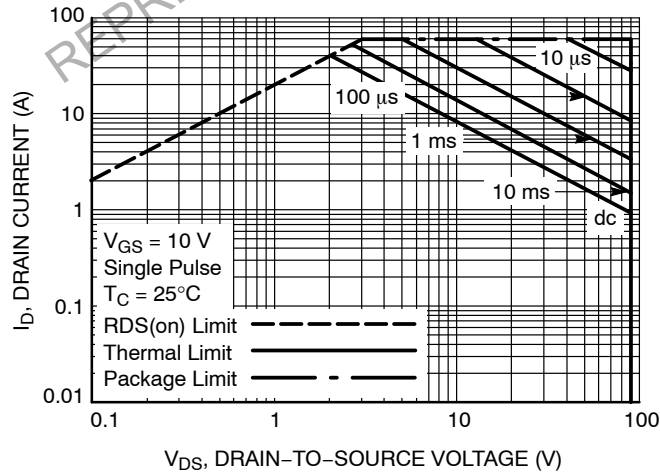


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

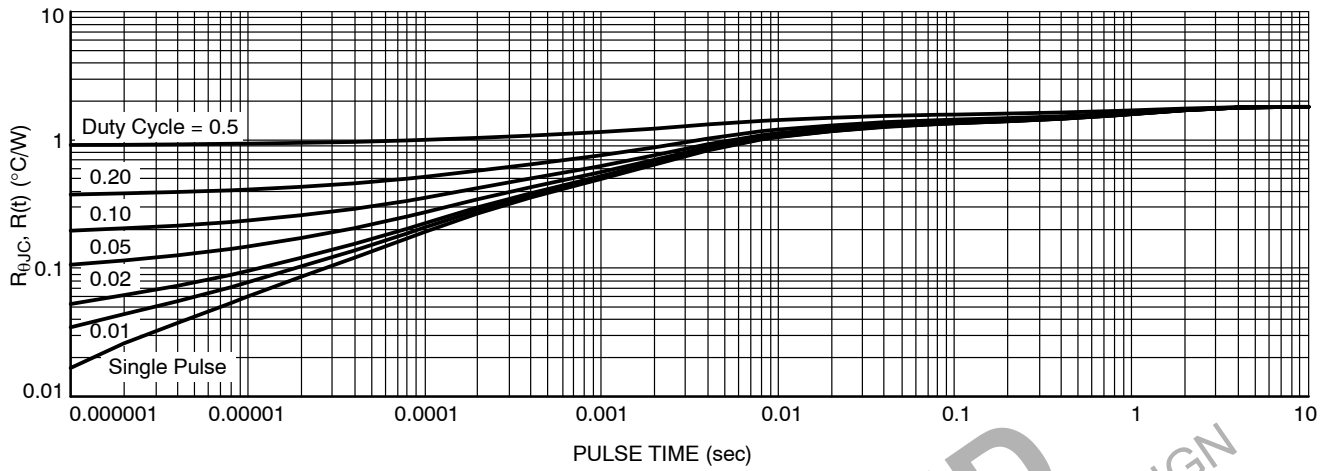


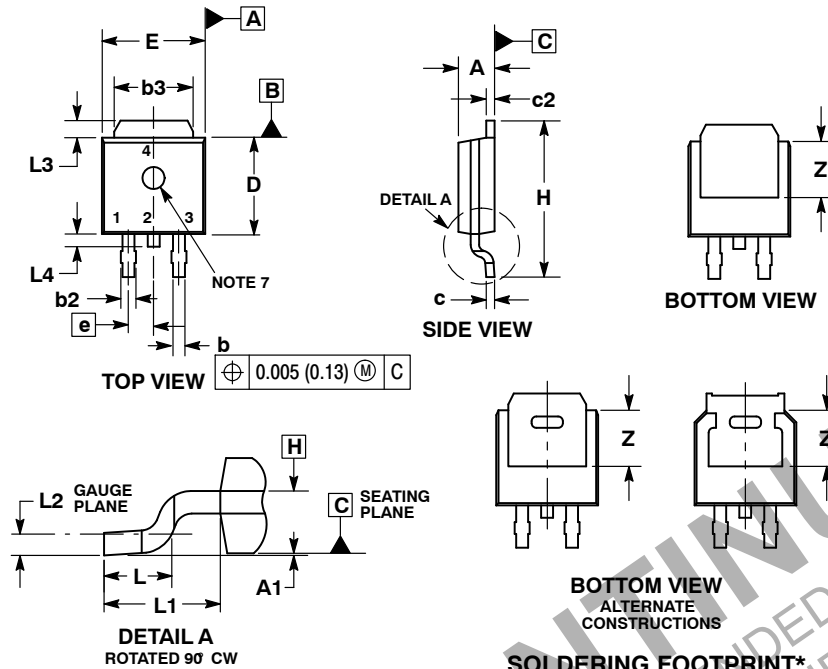
Figure 12. Thermal Response

DISCONTINUED
 THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN
 PLEASE CONTACT YOUR onsemi
 REPRESENTATIVE FOR INFORMATION

NVD6828NL

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE F



NOTES:

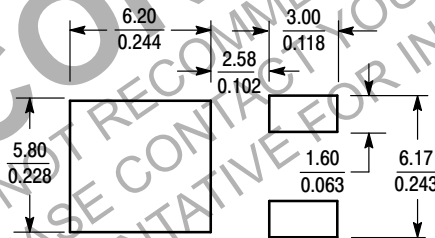
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.095	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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